

YJ Planar Schottky Barrier Diode Die Specification

30V 0.5A, 25mil, Schottky barrier diode die based on silicon planar process
Part No.: PSB025L030AS-180A

Main Products Characteristics

Maximum Ratings

Static Electrical Characteristics (Ta = 25°C)

Spec	Typical
34 V	39V

$I_F = 0.5A$

2%

Device Schematics and Outline Drawing

Die Thickness *

Die Size **

Top Metal Pad 22Mils 560um)

Active Area 18.8 Mils 478um)

Top Metal

Back Metal

Note: 1 * : Also can offer device with 8 mils thickness

2 **: Cutting street width is around 70um

Important Notice

Specification apply to die only. Actual performance may degrade when assembled.

does not guarantee device performance after assembly.

All operating parameters must be validated for each customer application by customer's technical experts.

Data sheet information is subjected to change without notice.

Recommended Storage Environment:

Store in original container, in dessicated nitrogen, with no contamination.

Shelf life for parts stored in above condition is 2 years.

If the storage is done in normal atmosphere shelf life is reduced to 6 months.

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